NPN Planar Type Silicon Darlington Transistor



# 2SC4005

# **Driver Applications**

## **Applications**

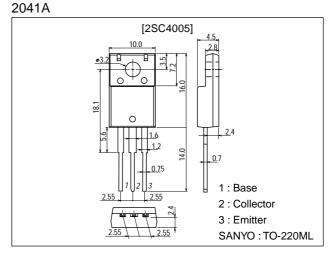
• Suitable for use in switching of L load (motor drivers, printer hammer drivers, relay drivers).

### Features

- · High DC current gain.
- · Large current capacity and wide ASO.
- On-chip Zener diode of 50±8V between collector and base.
- Uniformity in collector-to-base breakdown voltage due to accurate impurity diffusion process.
- · Large inductive load handling capability.
- · Micaless package facilitating mounting.

## **Package Dimensions**

unit:mm



# **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		42*	V
Collector-to-Emitter Voltage	VCEO		42*	V
Emitter-to-Base Voltage	VEBO		6	V
Collector Current	IC		2	Α
Collector Current (Pulse)	ICP		4	Α
Base Current	۱ <sub>B</sub>		0.4	А
Collector Dissipation	PC		2.0	W
		Tc=25°C	15	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

\* : On-chip Zener diode of 50±8V

#### Electrical Characteristics at Ta = 25°C

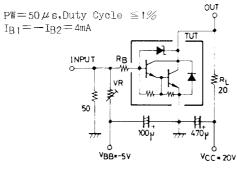
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V <sub>CB</sub> =30V, I <sub>E</sub> =0			10	μA
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =5V, I <sub>C</sub> =0			2	mA
DC Current Gain	hFE	V <sub>CE</sub> =5V, I <sub>C</sub> =1A	2000	4000		
Gain-Bandwidth Product	fT	V <sub>CE</sub> =5V, I <sub>C</sub> =1A		180		MHz
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =1A, I <sub>B</sub> =4mA		1.0	1.5	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =1A, I <sub>B</sub> =4mA			2.0	V

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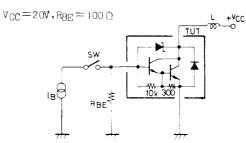
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onit
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =0.1mA, I <sub>E</sub> =0	42	50	58	V
Collector-to-Emitter Breakdown Voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> =1mA, R <sub>BE</sub> =∞	42	50	58	V
Inductive Load Handling Capability	Es/b	L=100mH, R <sub>BE</sub> =100Ω	25			mJ
Turn-ON Time	ton	See specified Test Circuit. V <sub>CC</sub> =20V, I <sub>C</sub> =1A, I <sub>B1</sub> =-I <sub>B2</sub> =4mA		0.2		μs
Storage Time	tstg	See specified Test Circuit. V <sub>CC</sub> =20V, I <sub>C</sub> =1A, I <sub>B1</sub> =-I <sub>B2</sub> =4mA		3.5		μs
Fall Time	t <sub>f</sub>	See specified Test Circuit. V <sub>CC</sub> =20V, I <sub>C</sub> =1A, I <sub>B1</sub> =-I <sub>B2</sub> =4mA		0.5		μs

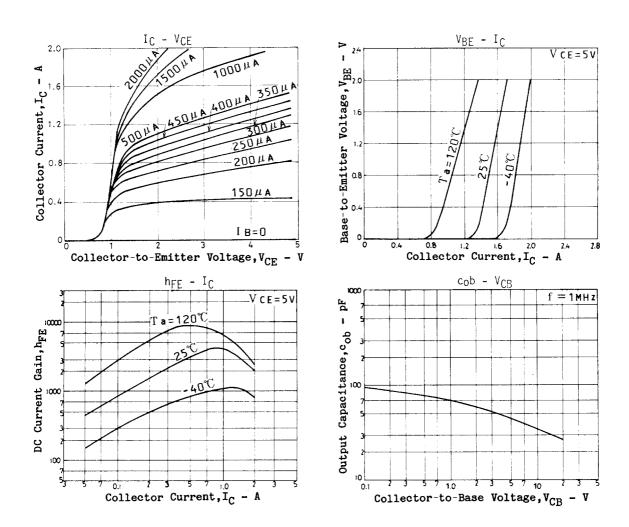
#### **Switching Time Test Circuit**

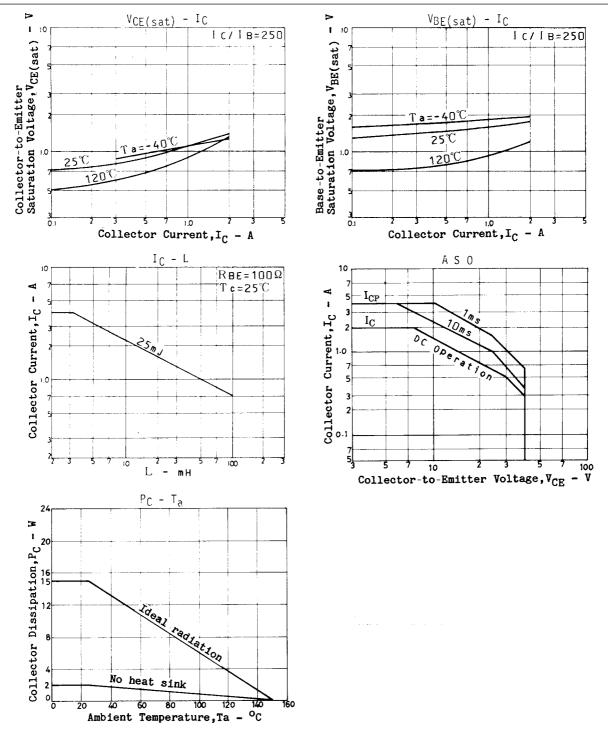


### Es/b Test Circuit



#### Unit (resistance: $\Omega$ , capacitance: F)





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